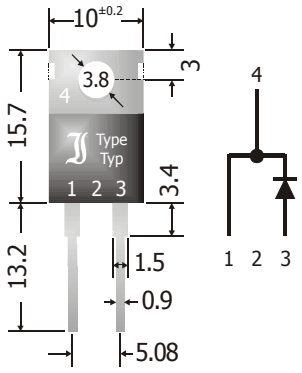
查询PT800A供应商

Diotec Semiconductor

PT800A ... PT800M

Silicon Rectifiers – Single Diode
Silizium-Gleichrichter – Einzeldiode

Version 2007-07-06



Dimensions - Maße [mm]

Nominal current Nennstrom	8 A
Repetitive peak reverse voltage Periodische Spitzensperrspannung	50...1000 V
Plastic case Kunststoffgehäuse	TO-220AC
Weight approx. Gewicht ca.	1.8 g
Plastic material has UL classification 94V-0 Gehäusematerial UL94V-0 klassifiziert	
Standard packaging in tubes Standard Lieferform in Stangen	

Maximum ratings and Characteristics **Grenz- und Kennwerte**

Type Typ	Repetitive peak reverse voltage Periodische Spitzensperrspannung V_{RRM} [V]	Surge peak reverse voltage Stoßspitzensperrspannung V_{RSM} [V]	Forward voltage Durchlass-Spannung V_F [V] [1]	
			I_F = 5 A	I_F = 8 A
PT800A	50	50	< 1.0	< 1.1
PT800B	100	100	< 1.0	< 1.1
PT800D	200	200	< 1.0	< 1.1
PT800G	400	400	< 1.0	< 1.1
PT800J	600	600	< 1.0	< 1.1
PT800K	800	800	< 1.0	< 1.1
PT800M	1000	1000	< 1.0	< 1.1

Max. average forward rectified current, R-load Dauergrenzstrom in Einwegschaltung mit R-Last	T_C = 100°C	I_{FAV}	8 A
Repetitive peak forward current Periodischer Spitzenstrom	f > 15 Hz	I_{FRM}	30 A [2]
Peak forward surge current, 50/60 Hz half sine-wave Stoßstrom für eine 50/60 Hz Sinus-Halbwelle	T_A = 25°C	I_{FSM}	135/150 A
Rating for fusing, t < 10 ms Grenzlastintegral, t < 10 ms	T_A = 25°C	i^2t	90 A^2s
Junction temperature – Sperrschichttemperatur Storage temperature – Lagerungstemperatur		T_j T_S	-50...+150°C -50...+175°C

1 T_j = 25°C
2 Max. temperature of the case T_C = 100°C – Max. Temperatur des Gehäuses T_C = 100°C

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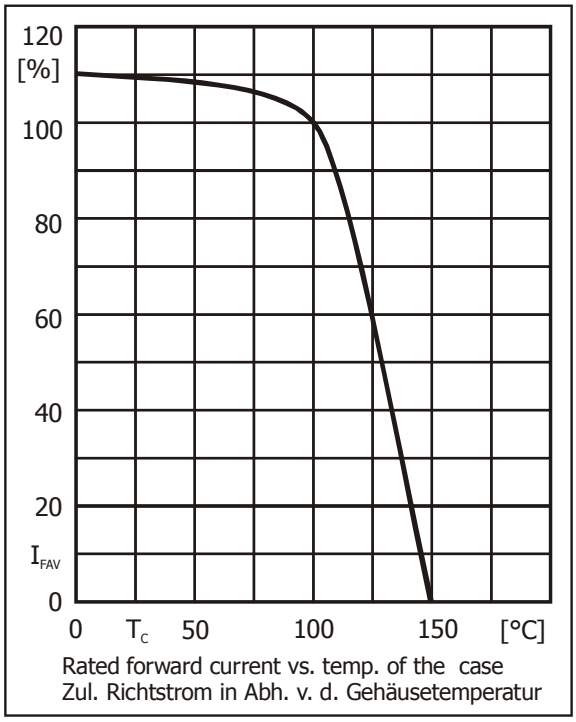
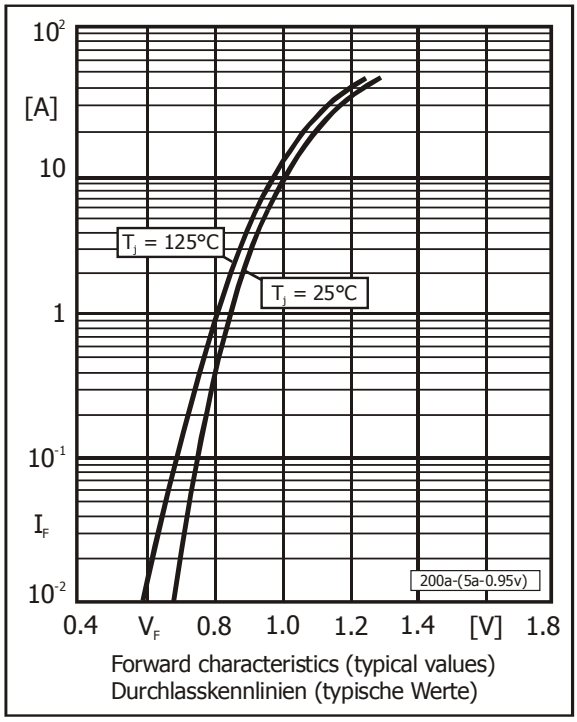
Characteristics			**Kennwerte**
Leakage current Sperrstrom	T_j = 25°C $V_R = V_{RRM}$	I_R	< 10 µA
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse		R_{thC}	< 2.5 K/W



Rated forward current vs. temp. of the case
Zul. Richtstrom in Abh. v. d. Gehäusetemperatur



Forward characteristics (typical values)
Durchlasskennlinien (typische Werte)

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